

High Voltage Switching Transistor (400V, 2A)

2SC3969 / 2SC5161

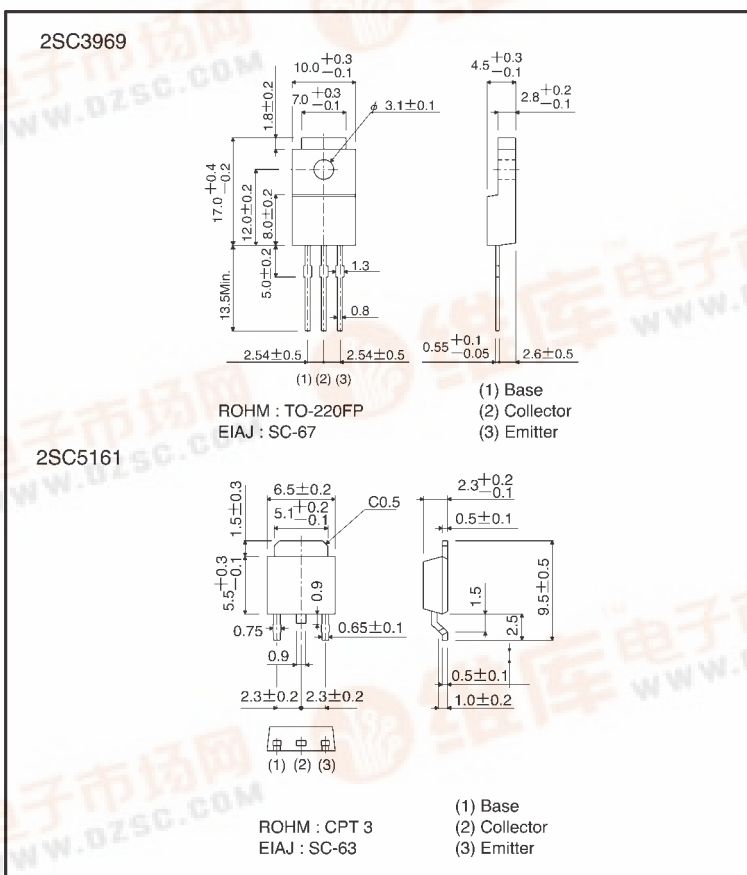
●Features

- 1) Low $V_{CE(sat)}$.
 $V_{CE(sat)} = 0.15V$ (Typ.)
($I_C / I_B = 1A / 0.2A$)
- 2) High breakdown voltage.
 $V_{CEO} = 400V$
- 3) Fast switching.
 $t_r = 1.0\mu s$
($I_C = 0.8A$)

●Structure

Three-layer, diffused planar type
NPN silicon transistor

●External dimensions (Units: mm)



Transistors

2SC3969 / 2SC5161

●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Collector-base voltage		V _{CBO}	400	V
Collector-emitter voltage		V _{CEO}	400	V
Emitter-base voltage		V _{EBO}	7	V
Collector current		I _C	2	A (DC)
		I _{CP}	4	A (Pulse) *
Collector power dissipation	2SC3969	P _C	2	W
			20	W (T _C =25℃)
	2SC5161		1	W
			10	W (T _C =25℃)
Junction temperature		T _j	150	℃
Storage temperature		T _{stg}	－55～＋150	℃

* Single pulse Pw=10ms

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	400	—	—	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	400	—	—	V	$I_C=1mA$
Collector-emitter voltage	$V_{CEO(SUS)}$	400	—	—	V	$I_C=1.0A, I_{B1}=0.1A, L=1mH$ *2
Emitter-base breakdown voltage	BV_{EBO}	7	—	—	V	$I_E=50\mu A$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB}=400V$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB}=7V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	1	V	$I_C/I_B=1A/0.2A$
Base-emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C/I_B=1A/0.2A$
DC current transfer ratio	h_{FE}	25	—	50	—	$V_{CE}=5V, I_C=0.1A$
Transition frequency	f_r	—	10	—	MHz	$V_{CE}=10V, I_E=-0.1A, f=5MHz$ *1
Output capacitance	C_{ob}	—	30	—	pF	$V_{CB}=10V, I_E=0A, f=1MHz$
Turn-on time	t_{ON}	—	—	1	μs	$I_C=0.8A, R_L=250\Omega$
Storage time	t_{stg}	—	—	2.5	μs	$I_{B1}=-I_{B2}=0.08A$
Fall time	t_f	—	—	1	μs	$V_{CC}=200V$ Refer to measurement circuit diagram

*1 Measured using pulse current

*2 2SC3969

●Packaging specifications and h_{FE}

Type	h_{FE}	Package name	Bulk	Taping
		Code		TL
		Basic ordering unit (pieces)	500	2500
2SC3969	B		○	—
2SC5161	B		—	○

h_{FE} values are classified as follows :

Item	B
h_{FE}	25~50

●Electrical characteristic curves

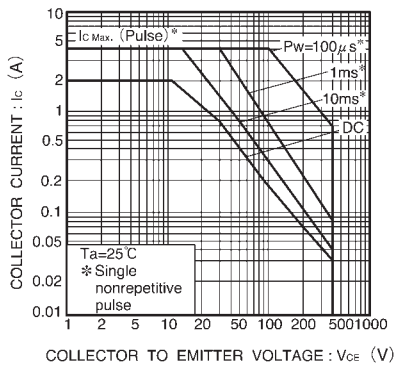


Fig.1 Safe operating area (2SC3969)

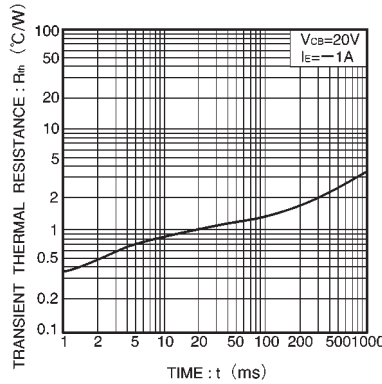


Fig.2 Transient thermal resistance (2SC3969)

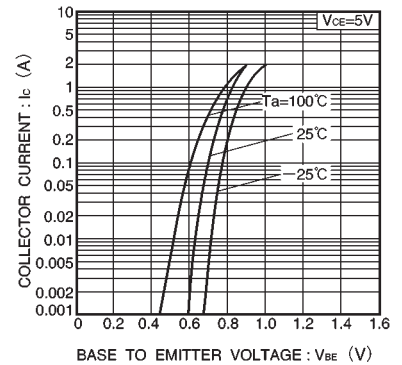


Fig.3 Grounded emitter propagation characteristics

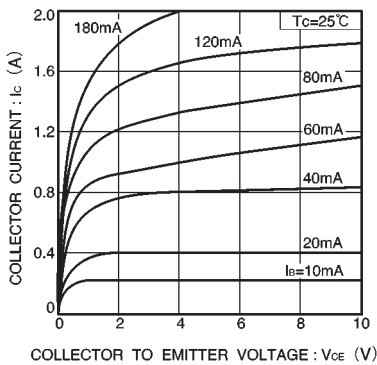


Fig.4 Grounded emitter output characteristics

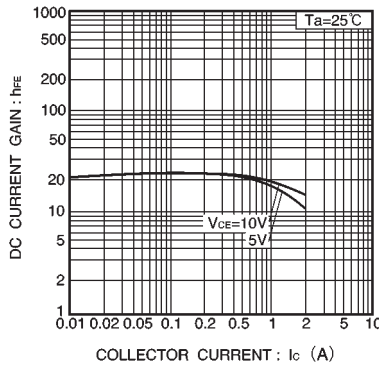


Fig.5 DC current gain vs. collector current (I)

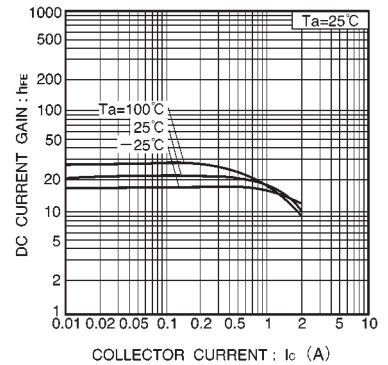


Fig.6 DC current gain vs. collector current (II)

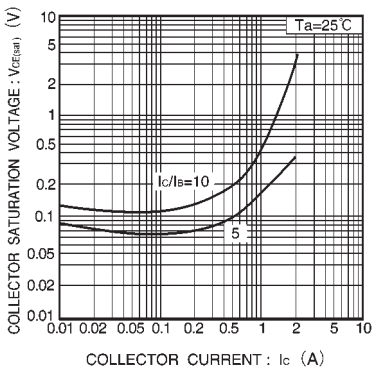


Fig.7 Collector-emitter saturation voltage vs. collector current

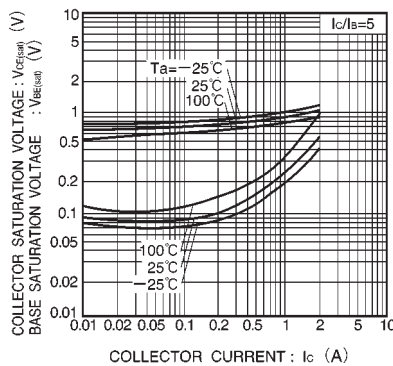


Fig.8 Collector-emitter saturation voltage vs. collector current
Base-emitter saturation voltage vs. collector current

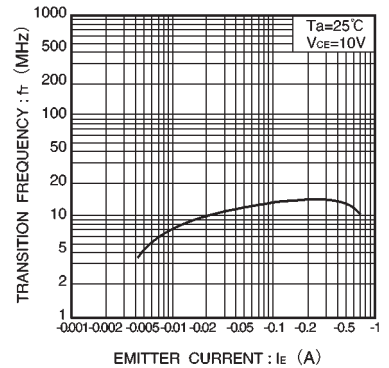


Fig.9 Gain bandwidth product vs. emitter current

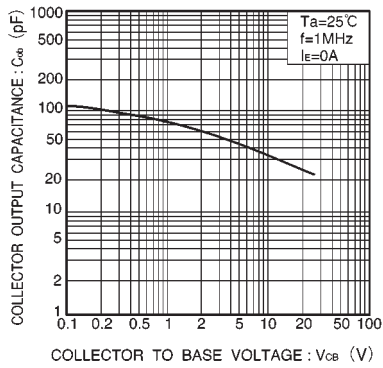


Fig.10 Collector output capacitance vs. collector-base voltage

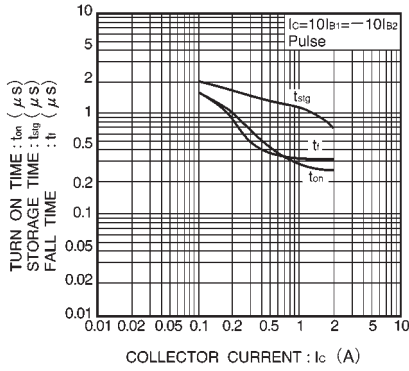


Fig.11 Switching time vs. collector current

● Switching characteristics measurement circuit

